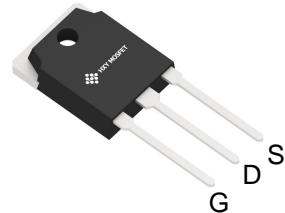




## Description

The HXY28N50TP uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.



**TO-3P  
(TO-3P-3)**

## General Features

$V_{DS} = 500V, I_D = 28A$

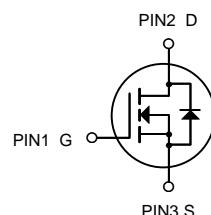
$R_{DS(ON)} < 180m\Omega$  @  $V_{GS}=10V$

## Application

High efficiency switch mode power supplies

Power factor correction

Electronic lamp ballast



N-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Marking	Units Tube
HXY28N50TP	TO-3P(TO-3P-3)	HXY 28N50 YYYY	50

## Absolute Maximum Ratings@ $T_j=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	500	V
V <sub>GS</sub>	Gate-Source Voltage	$\pm 20$	V
I <sub>D</sub> @ $T_c=25^\circ C$	Drain Current	28	A
I <sub>DM</sub>	Pulsed Drain Current <sup>1</sup>	112	A
P <sub>D</sub> @ $T_c=25^\circ C$	Total Power Dissipation	312.5	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C



**Electrical Characteristics ( $T_c=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage <sup>(Note 1)</sup>	$\text{BV}_{\text{DSS}}$	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{D}}=250\mu\text{A}$	500	-	-	V
Zero Gate Voltage Drain Current	$\text{I}_{\text{DSS}}$	$\text{V}_{\text{DS}}=500\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate-Body Leakage Current	$\text{I}_{\text{GSS}}$	$\text{V}_{\text{GS}}=\pm20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	$\pm100$	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_{\text{D}}=250\mu\text{A}$	2.0	-	4.0	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS(ON)}}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_{\text{D}}=14\text{A}$	-	150	180	$\text{m}\Omega$
Forward Transconductance	$\text{g}_{\text{FS}}$	$\text{V}_{\text{DS}}=40\text{V}, \text{I}_{\text{D}}=14\text{A}$	-	25	-	S
<b>Dynamic Characteristics</b>						
Input Capacitance	$\text{C}_{\text{iss}}$	$\text{V}_{\text{DS}}=25\text{V}, \text{V}_{\text{GS}}=0\text{V},$ $\text{F}=1.0\text{MHz}$	-	4500	-	PF
Output Capacitance	$\text{C}_{\text{oss}}$		-	320	-	PF
Reverse Transfer Capacitance	$\text{C}_{\text{rss}}$		-	20	-	PF
<b>Switching Characteristics</b>						
Turn-on Delay Time	$\text{t}_{\text{d(on)}}$	$\text{V}_{\text{DD}}=400\text{V}, \text{I}_{\text{D}}=28\text{A}$ $\text{R}_{\text{G}}=10 \Omega$ <sup>(Note 2)</sup>	-	40	-	nS
Turn-on Rise Time	$\text{t}_r$		-	70	-	nS
Turn-Off Delay Time	$\text{t}_{\text{d(off)}}$		-	170	-	nS
Turn-Off Fall Time	$\text{t}_f$		-	55	-	nS
Total Gate Charge	$\text{Q}_{\text{g}}$	$\text{V}_{\text{DS}}=400\text{V}, \text{I}_{\text{D}}=28\text{A},$ $\text{V}_{\text{GS}}=10\text{V}$ <sup>(Note 2)</sup>	-	110	-	nC
Gate-Source Charge	$\text{Q}_{\text{gs}}$		-	15	-	nC
Gate-Drain Charge	$\text{Q}_{\text{gd}}$		-	40	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$\text{V}_{\text{SD}}$	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_{\text{S}}=14\text{A}$	-		1.4	V
Diode Forward Current <sup>(Note 2)</sup>	$\text{I}_{\text{S}}$		-	-	28	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .



## Typical Characteristics

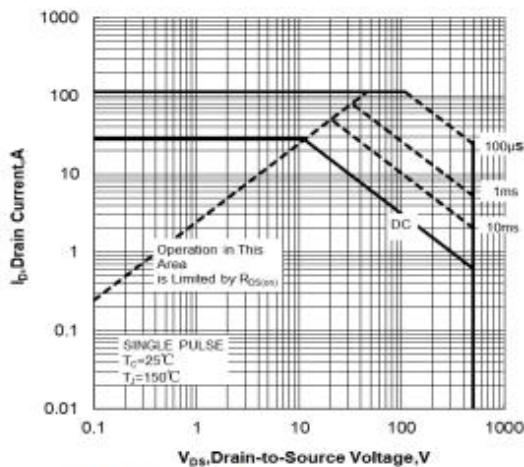


Figure 1 Maximum Forward Bias Safe Operating Area

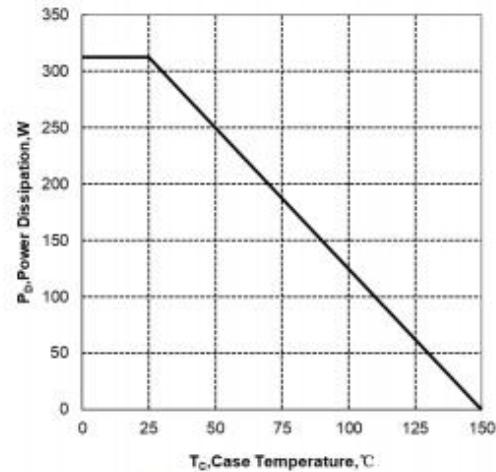


Figure 2 Maximum Power dissipation vs Case Temperature

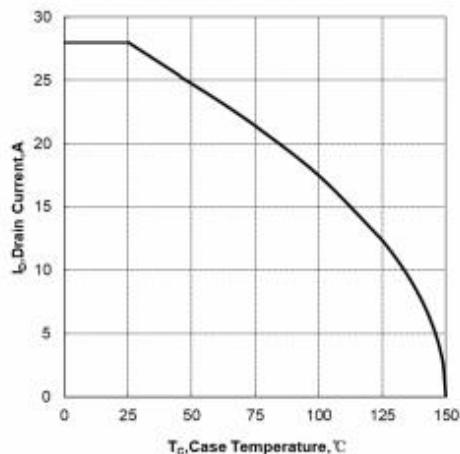


Figure 3 Maximum Continuous Drain Current vs Case Temperature

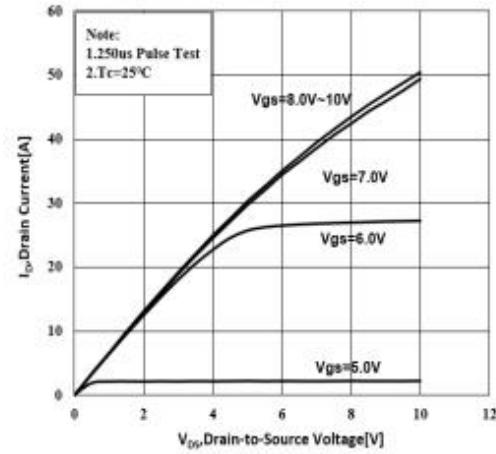


Figure 4 Typical Output Characteristics

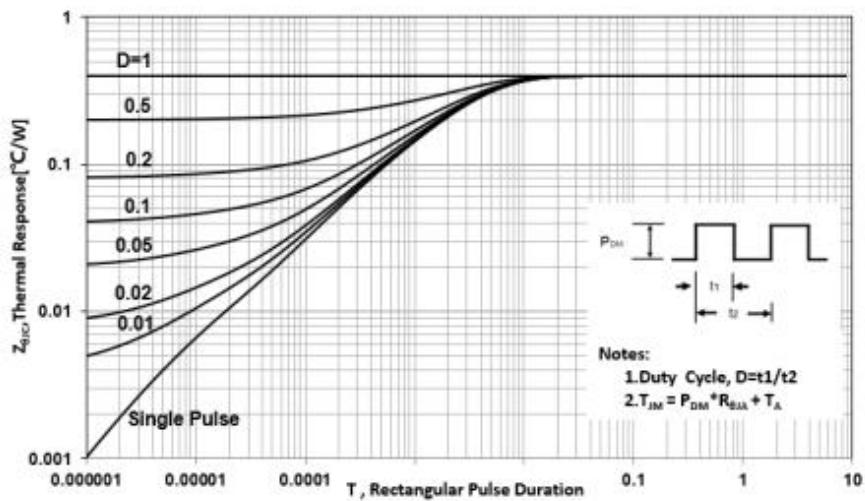


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

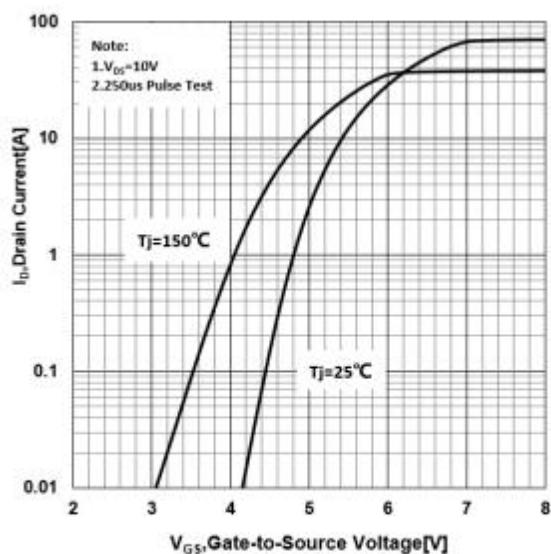


Figure 6 Typical Transfer Characteristics

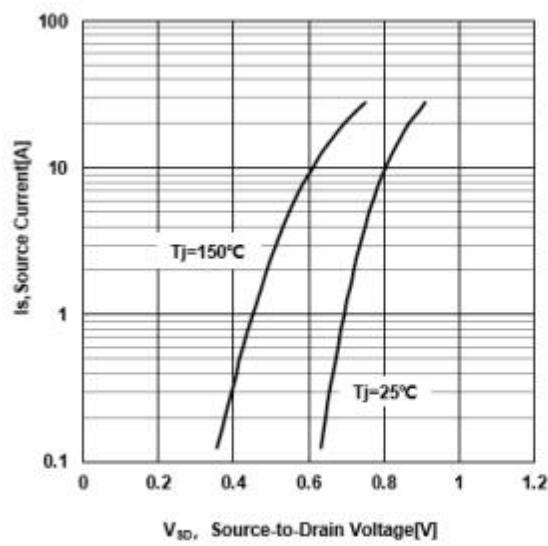


Figure 7 Typical Body Diode Transfer Characteristics

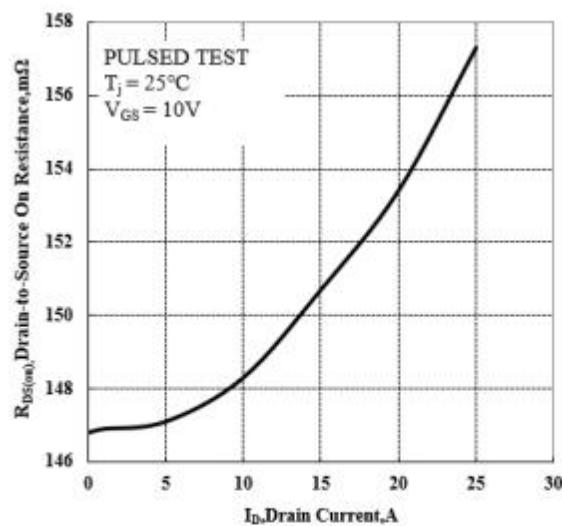


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

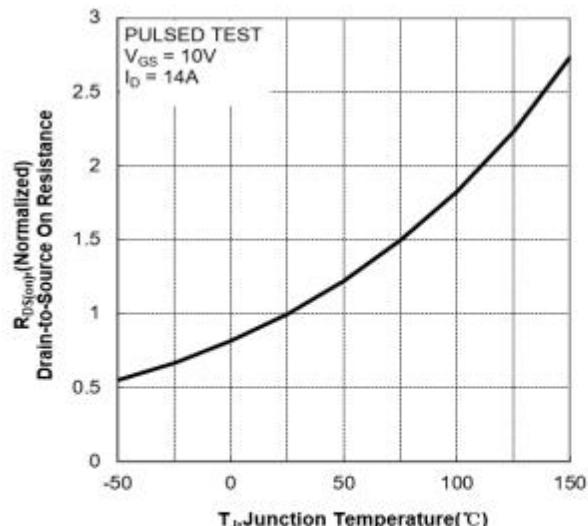


Figure 9 Typical Drian to Source on Resistance vs Junction Temperature

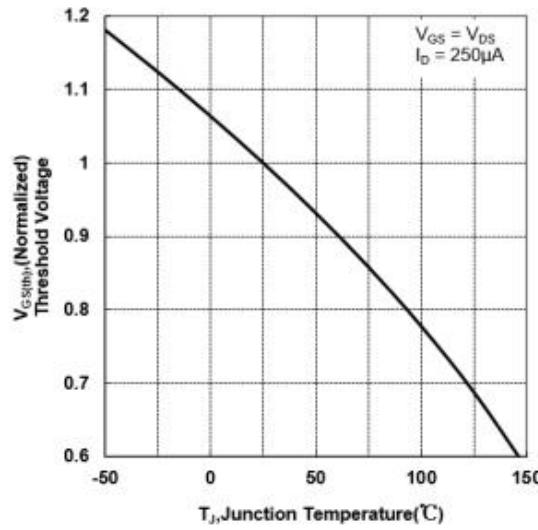


Figure 10 Typical Threshold Voltage vs Junction Temperature

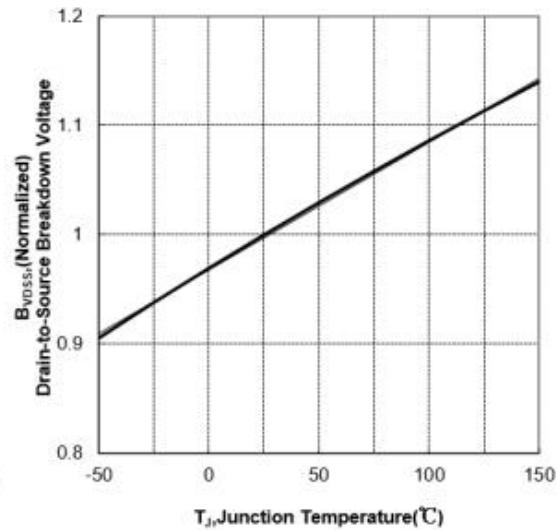


Figure 11 Typical Breakdown Voltage vs Junction Temperature

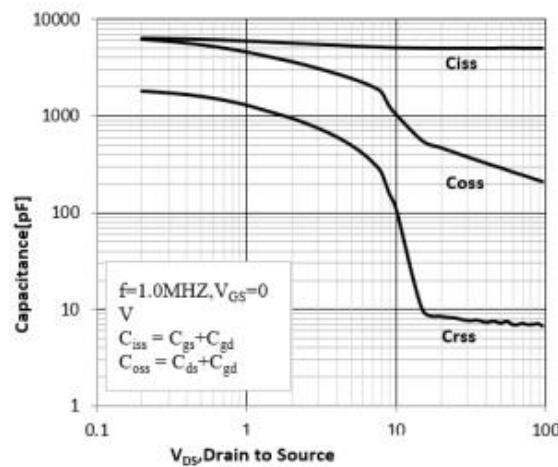


Figure 12 Typical Capacitance vs Drain to Source Voltage

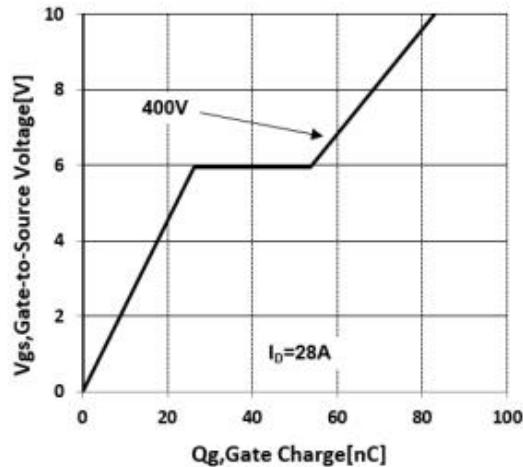
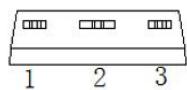
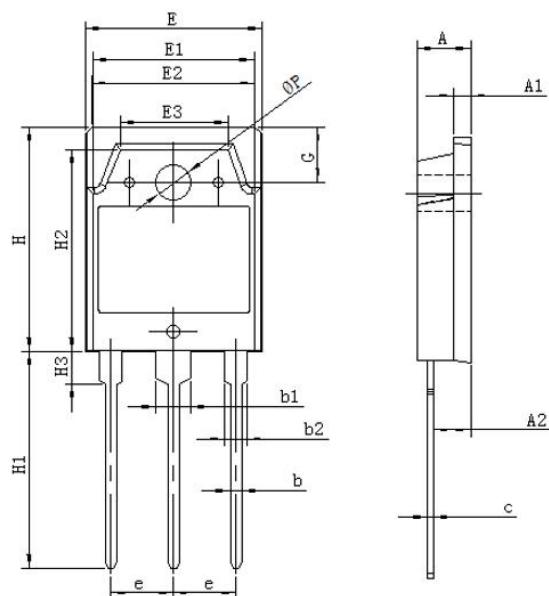


Figure 13 Typical Gate Charge vs Gate to Source Voltage



## Package Information

**TO-3P  
(TO-3P-3)**



Symbol	单位 mm		
	Min	Nom	Max
A	4.60	4.80	5.00
A1	1.3	1.5	1.7
A2	1.20	1.40	1.60
b	0.80	1.0	1.20
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c	0.50	0.60	0.70
e	5.25	5.45	5.65
E	15.2	15.6	16.0
E1	13.2	13.4	13.6
E2	13.1	13.3	13.5
E3	9.1	9.3	9.5
H	19.8	20.0	20.2
H1	20.1	20.3	20.5
H2	18.5	18.7	18.9
H3	3.2	3.5	3.8
G	4.8	5.0	5.2
ΦP	3.00	3.20	3.40



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